



High-Performance Differential Fanout Buffer

Features

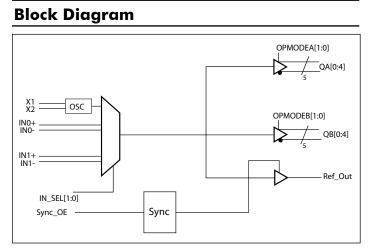
- 10 Differential Outputs with Two Banks
- User Configurable Output Signaling Standard for Each Bank: LVDS or LVPECL or HCSL
- LVCMOS Reference Output up to 200MHz
- Up to 1.5GHz Output Frequency for Differential Outputs
- Ultra-Low Additive Phase Jitter:
 - <0.02ps (typ) (Differential 156.25MHz, 12KHz to 20MHz Integration Range)
 - <0.01ps (typ) (Differential 156.25MHz, 10kHz to 1MHz</p> Integration Range)
- Selectable Reference Inputs Support Either Single-Ended or Differential or Xtal
- Low Skew Between Outputs within Banks (<40ps)
- Low Delay from Input to Output (Tpd typ. <0.9ns)
- Separate Input Output Supply Voltage for Level Shifting
- 2.5V/3.3V Power Supply
- Industrial Temperature Support
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) •
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green): 48-Pin, TOFN (ZD)

Applications

- Networking Systems Including Switches and Routers
- High-Frequency Backplane Based Computing and Telecom Platforms

Description

The DIODES[™] PI6C49S1510B is a high-performance fanout buffer device which supports up to 1.5GHz frequency. It also integrates a unique feature with user-configurable output signaling standards on per bank basis, which provides great flexibility to users. The device also uses Diodes' proprietary input detection technique to make sure illegal input conditions are detected and reflected by output states. This device is ideal for systems that must distribute low jitter clock signals to multiple destinations.



Notes:

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- DIODES is a trademark of Diodes Incorporated in the United States and other countries.

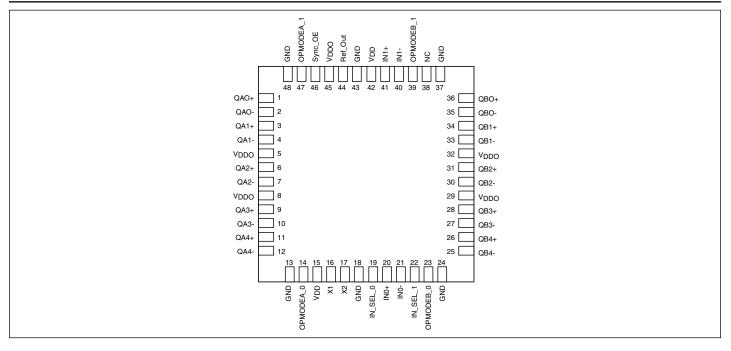
The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries.

^{1.} No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.





Pin Configuration



Pin Description

Pin #	Pin Name	,	Гуре	Description		
1, 2	QA0+	Output		Bank A differential output pair 0.		
1, 2	QA0-		uipui	Pin selectable LVPECL/LVDS/HCSL interface levels.		
2 4	QA1+		utout	Bank A differential output pair 1.		
3, 4	QA1-		utput	Pin selectable LVPECL/LVDS/HCSL interface levels.		
5, 8, 29, 32, 45	VDDO	F	ower	Power supply pins for IO		
QA2+				Bank A differential output pair 2.		
6,7	QA2-	Output		Pin selectable LVPECL/LVDS/HCSL interface levels.		
0.10	QA3+	Output		Bank A differential output pair 3. Pin selectable LVPECL/LVDS/HCSL interface levels.		
9, 10	QA3-					
11 12	QA4+			Bank A differential output pair 4.		
11, 12	QA4-	Output		Pin selectable LVPECL/LVDS/HCSL interface levels.		
13, 18, 24, 37, 43, 48	GND	F	Power	Power supply ground		
14, 47	OPMODEA	Input Pulldown		Output mode select for Bank A. See Table 2 for functions, LVCMOS/LVTTL interface levels		
15, 42	V _{DD}	F	ower	Power supply pins		
16	X1		nput	XTAL input, can also be used as single ended input pin		
17	X2	C	utput	XTAL output. If X1 is used as a single ended input pin, X2 is to be left open		





Pin Description Cont.

Pin #	Pin Name	r	Гуре	Description	
19, 22	IN_SEL	Input	Pulldown	Input clock select. See Table 1 for function. LVCMOS/LVTTL interface levels.	
20	IN0+	Input	Pulldown	Reference input 0, internal bias to $0.33V_{DD}$	
21	IN0-	Input	Pullup/ Pulldown	Inverted reference input 0, internal bias to $0.42V_{\text{DD}}$	
23, 39	OPMODEB	Input	Pulldown	Output mode select for Bank B. See Table 2 for functions, LVCMOS/LVTTL interface levels	
26.25	QB4+			Bank B differential output pair 4.	
26, 25	QB4-		output	Pin selectable LVPECL/LVDS/HCSL interface levels.	
	QB3+			Bank B differential output pair 3.	
28, 27	QB3-		utput	Pin selectable LVPECL/LVDS/HCSL interface levels.	
21. 20	QB2+			Bank B differential output pair 2.	
31, 30	QB2-		utput	Pin selectable LVPECL/LVDS/HCSL interface levels.	
24.22	QB1+			Bank B differential output pair 1.	
34, 33	QB1-		utput	Pin selectable LVPECL/LVDS/HCSL interface levels.	
26.25	QB0+			Bank B differential output pair 0.	
36, 35	QB0-		output	Pin selectable LVPECL/LVDS/HCSL interface levels.	
38	NC		_	Do not connect	
40	IN1-	Input	Pullup/ Pulldown	Inverted reference input, internal bias to $0.42 V_{\mbox{\tiny DD}}$	
41	IN1+	Input	Pulldown	Reference input 1, internal bias to $0.33V_{\text{DD}}$	
44	Ref_Out	C	utput	Reference output, CMOS	
46	Sync_OE	Input	Pulldown	Synchronous output enable for Ref_Out. See Table 3 for functions.	





Function Table

Table 1: Input Select Function

IN_SEL [1]	IN_SEL [0]	Function
0	0	IN0 is the selected reference input
0	1	IN1 is the selected reference input
1	X	XTAL is the selected input

Table 2: Output Mode Select Function

OPMODEA/B [1]	OPMODEA/B [0]	Output Bank A/Bank B Mode
0	0	LVPECL
0	1	LVDS
1	0	HCSL
1	1	Hi-Z

Table 3: Reference Output Enable Function

Sync_OE	Ref_Out
0	Hi-Z
1	Output Enabled

Table 4: Illegal Input Level Function

Input Illegal Status	Output Status
Input Open	Logic Low
Input Both High	Logic Low
Input Both Low	Logic Low





Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature
Supply Voltage to Ground Potential (V_{DD,}V_{DDO}) -0.5V to +4.6V
Inputs (Referenced to GND)0.5V to $V_{\mbox{\scriptsize DD}}\mbox{+}0.5V$
Clock Output (Referenced to GND)0.5V to $V_{\mbox{\scriptsize DD}}\mbox{+}0.5V$
Latch up200mA
ESD Protection (Input) 2000V min (HBM)
Junction Temperature

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Power Supply Characteristics and Operating Conditions

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{DD}	Core Supply Voltage	—	2.375	_	3.465	V
V _{DDO}	Output Supply Voltage	—	2.375		3.465	V
I_{DD}	Core Power Supply Current	—	—	90	120	
	Output Power Supply Current	All LVPECL outputs unloaded	_	150	190	mA
I _{DDO}		All LVDS outputs loaded		110	130	11171
		All HCSL outputs unloaded		80	140	
T _A	Ambient Operating Temperature ⁽¹⁾	_	-40	_	85	°C
Тв	PCB Operating Temperature ⁽¹⁾	_	-40	_	105	°C

Note 1: Either T_A or T_B used as operating condition.

DC Electrical Specifications - Differential Inputs

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{IH}	Input High Current	Input = V_{DD}	_	_	150	μΑ
I _{IL}	Input Low Current	Input = GND	-150	_	_	μΑ
CIN	Input Capacitance	_	_	3	_	pF
V _{IH}	Input High Voltage	_	_	_	V _{DD} +0.3	V
V _{IL}	Input Low Voltage	_	-0.3	_	_	V
V _{ID}	Input Differential Amplitude PK-PK	_	0.15	_	1.3	V
V _{CM}	Common Model Input Voltage	_	0.25	_	V _{DD} -1.2	V
ISO _{MUX}	MUX Isolation	_		-89		dBc





Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
I _{IH}	Input High Current	Input = V_{DD}	_	_	150	μΑ
I _{IL}	Input Low Current	Input = GND	-150	_	_	μΑ
V_{IH}	Input High Voltage	V _{DD} =3.3V	2.0	_	V _{DD} +0.3	V
V_{IL}	Input Low Voltage	$V_{DD}=3.3V$	-0.3	_	0.8	V
$V_{\rm IH}$	Input High Voltage	$V_{DD}=2.5V$	1.7	_	V _{DD} +0.3	V
V_{IL}	Input Low Voltage	$V_{DD}=2.5V$	-0.3	_	0.7	V

DC Electrical Specifications - LVCMOS Inputs

DC Electrical Specifications - LVPECL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{он}	Output High Voltage	—	V _{DDO} -1.4	_	V_{DDO} -0.9	V
V _{OL}	Output Low Voltage	_	V _{DDO} -2.2	_	V_{DDO} -1.7	V

DC Electrical Specifications - LVDS Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{он}	Output High Voltage	—	_	1.43		V
V _{OL}	Output Low Voltage	_	_	1.0		V
Vocm	Output Commode Voltage	_		1.25		V
DVocm	Change in Vocm Between Completely Output States	_	_	_	50	mV
Ro	Output Impedance	_	85	—	140	W

DC Electrical Specifications – HCSL Outputs

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
V _{OH}		2.5V	480	_	900	mV
	Output High Voltage	3.3V	600	850	1050	mV
V _{OL}	Output Low Voltage	—	-150	_	150	mV





Parameter	Description	Conditions	Min.	Тур.	Max.	Units
17	Output High Voltage	$V_{\rm DDO}{=}3.3V$ ±5%, $I_{\rm OH{\scriptscriptstyle =}}$ 8mA	2.3	_	_	V
V _{OH}		$V_{\rm DDO}{=}2.5V$ ±5%, $I_{\rm OH{\scriptscriptstyle =}}8mA$	1.5	_	_	V
V _{ol}	Output Low Voltage	$V_{\rm DDO}{=}3.3V$ ±5%, $I_{\rm OL{=}}$ -8mA	_	_	0.5	V
		$V_{\rm DDO}{=}2.5V$ ±5%, $I_{\rm OL{\scriptscriptstyle =}}$ -8mA	_	_	0.4	V
17	Output High Voltage	$V_{\rm DDO}{=}3.3V$ ±5%, $I_{\rm OH{\scriptscriptstyle =}}24mA$	2.1	_		V
V _{OH}		$V_{\rm DDO}{=}2.5V$ ±5%, $I_{\rm OH{\scriptscriptstyle =}}$ 16mA	1.5	_		V
37	Outrast Lass Walts as	$V_{\rm DDO}{=}3.3V$ ±5%, $I_{\rm OL{=}}$ -24mA	_	_	1	V
V _{OL}	Output Low Voltage	$V_{\rm DDO}\mbox{=}2.5V$ ±5%, $I_{\rm OL\mbox{=}}\mbox{-}16mA$	_	_	0.8	V
D	Output Impedance	$V_{DDO} = 3.3V \pm 5\%$	_	17		Ω
R _{IUT}		$V_{DDO} = 2.5V \pm 5\%$	_	22		Ω

DC Electrical Specifications – LVCMOS Outputs

AC Electrical Specifications – Differential Outputs

Parameter	Description	Conditions		Min.	Тур.	Max.	Units	
г	Clock Output Frequency	LVPECL, LVDS	_	_	_	1500	MHz	
F _{OUT}		HCSL	_	_		250		
			LVPECL	120	150	300	ps	
T_r	Output Rise Time	From 20% to 80%	LVDS	120	150	300		
			HCSL	300		700		
			LVPECL	120	150	300		
$T_{\rm f}$	Output Fall Time	From 80% to 20%	LVDS	120	150	300	ps	
			HCSL	300		700		
	Output Duty Cycle	Frequency <650MHz, $V_{ID} \ge 400 \text{mV}$	LVPECL, HCSL (<250MHz)	48	_	52	_	
			LVDS	47	_	53		
		Frequency <1GHz,	LVPECL	45	_	55]	
T _{ODC}		$V_{\rm ID} \geq 400 mV$	LVDS	45		55	- %	
		Frequency <1.5GHz, $V_{ID} \ge 400 \text{mV}$	LVDS	40	_	60		
		Frequency <1.5GHz, $V_{ID} \ge 400 \text{mV}$	LVPECL	40		60		
		LVPECL Outputs @ <1	lGHz	500		1100		
V		LVPECL Outputs @ >1	GHz	400		1000	mV	
V_{PP}	Output Swing Single-Ended	LVDS Outputs @ <1Gl	Hz	250		600	mV	
		LVDS Outputs @ >1GF	Ηz	250	_	550		





Parameter	Description	Conditions	Min.	Тур.	Max.	Units
Tj	Buffer Additive Jitter RMS	156.25MHz, 12kHz to 20MHz		0.02	_	ps
		156.25MHz, 10kHz to 1MHz	_	0.01		ps
V _{CROSS}	Absolute Crossing Voltage	HCSL	_	460	_	mV
DV _{CROSS}	Total Variation of Crossing Voltage	HCSL	_	_	140	mV
T _{sk}	Output Skew	10 outputs devices, outputs in same bank with same load at DUT	_	15	40	ps
		LVPECL, LVDS @ 3.3V, 100MHz	_	570	_	ps
T _{PD} Propagation Delay		HCSL @ 3.3V, 100MHz	_	900	_	ps
T _{OD}	Valid to HiZ		_	_	80	ns
T _{OE}	HiZ to valid		_	_	80	ns
T _{P2P Skew}	Part-to-Part Skew ⁽¹⁾		_	80	120	ps

AC Electrical Specifications – Differential Outputs Cont.

AC Electrical Specifications – CMOS

Parameter	Description	Conditions	Min.	Тур.	Max.	Units
Г		XTAL input	10	_	50	MHz
F _{OUT}	Ref_Out Frequency	Reference input			200	MHz
Tj	Deffer Addition litter DMC	XTAL input		0.3		ps
	Buffer Additive Jitter RMS	Reference input	_	0.03	_	ps
$t_{r\prime}t_f$	Rise Time, Fall Time	$C_L = 10 pF$	_	1.5	_	ns
T _{ODC}	Output Duty Cycle	$C_L = 10 pF$	45	_	55	%
t _{PD}	Propagation Delay	3.3V, 25MHz	_	2200	_	ps
ts	Setup Time	_	300	_	_	ps
t _{SOD}	Clock Edge to Output Disable	Ref_Out	2	_	4	cycles
t _{SOE}	Clock Edge to Output Enable	Ref_Out	2	_	4	cycles
Notes:						

Notes:

1. This parameter is guaranteed by design.





Crystal Characteristics

Parameter	Min.	Typ.	Max.	Units
Mode of Oscillation		Fundamental		
Frequency Range	10		50	MHz
Equivalent Series Resistance (ESR)	_	_	70	Ω
Shunt Capacitance	_	_	7	pF
Load Capacitance	10	_	18	pF
Drive Level			500	μW

Recommended Crystals

Diodes recommends:

a) GC2500003 XTAL 49S/SMD(4.0 mm), 25M, CL=18pF, ±30ppm

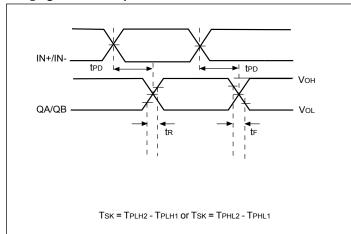
b) FY2500091, SMD 5x3.2(4P), 25M, CL=18pF, ±30ppm

c) FL2500047, SMD 3.2x2.5(4P), 25M, CL=18pF, ±20ppm

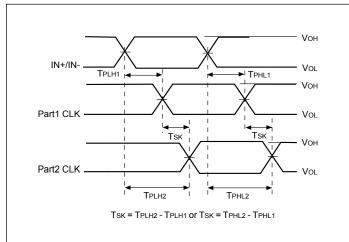




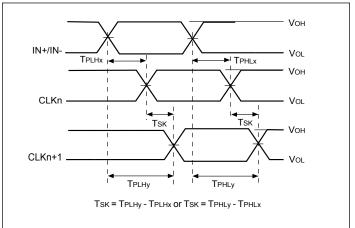
Propagation Delay (TPD)



Part-to-Part Skew



Output Skew (Tsk)

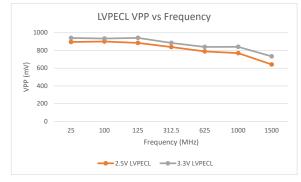




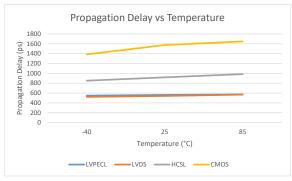
A Product Line of Diodes Incorporated

PI6C49S1510B

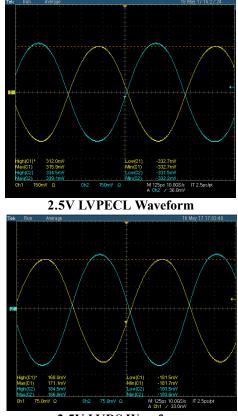
LVPECL/LVDS Output Swing vs Frequency



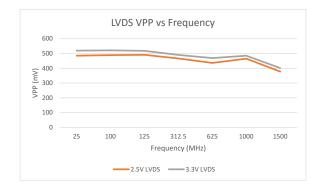
Propagation Delay vs Temperature

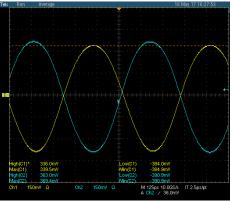


1.5GHz LVPECL/LVDS Waveform

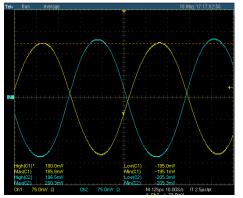


2.5V LVDS Waveform





3.3V LVPECL Waveform



3.3V LVDS Waveform

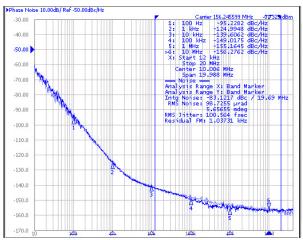




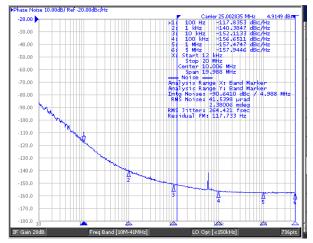
Phase Noise and Additive Jitter

Output Phase Noise (Dark Blue) vs Input Phase Noise (Light Blue)

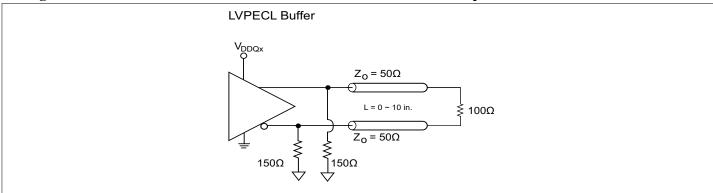
Additive jitter is calculated at 156.25MHz ~ 27fs RMS (12kHz to 20MHz). Additive jitter = $\sqrt{(\text{Output jitter}^2 - \text{Input jitter}^2)}$



Total Phase Jitter with 25MHz XTAL ~ 264fs RMS (12kHz ~ 20MHz)



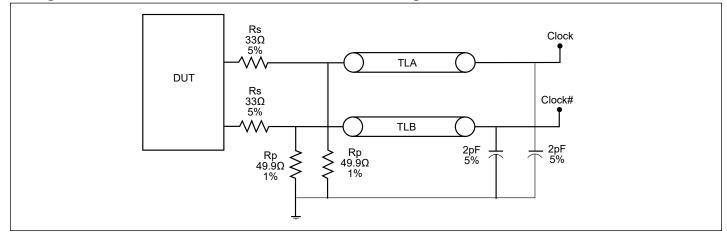
Configuration Test Load Board Termination for LVPECL/LVDS Outputs



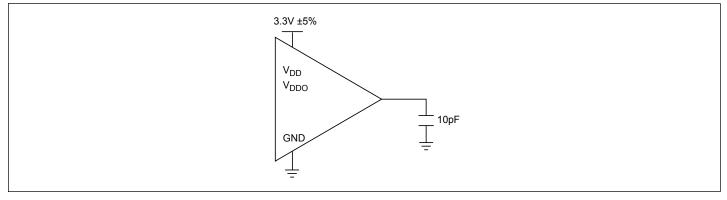




Configuration Test Load Board Termination for HCSL Outputs



Configuration Test Load Board Termination for LVCMOS Outputs







Application Information

Wiring the Differential Input to Accept Single-Ended Levels

Figure 1 shows how the differential input can be wired to accept single-ended levels. The reference voltage $V_{REF} = V_{DD}/2$ is generated by the bias resistors R1, R2, and C1. This bias circuit should be located as close as possible to the input pin. The ratio of R1 and R2 might require to be adjusted to position the V_REF in the center of the input voltage swing. For example, if the input clock swing is only 2.5V, V_{DD} = 3.3V, V_REF should be 1.25V and R2/R1 = 0.609.

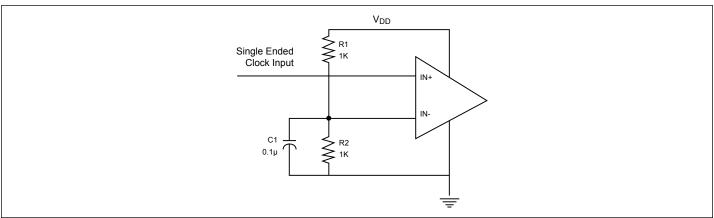
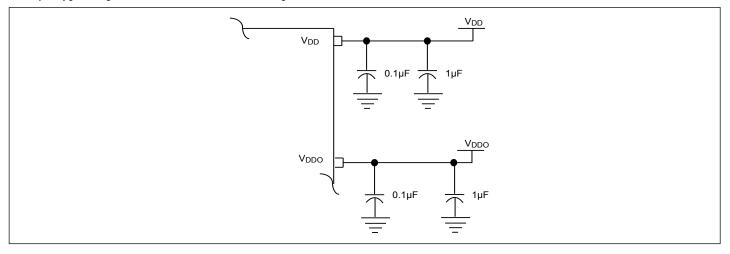


Figure 1. Single-Ended Input to Differential Input Device

Power Supply Filtering Techniques

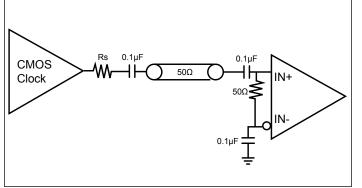
As in any high-speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. All power pins should be individually connected to the power supply plane through vias, and 0.1µF and 1µF bypass capacitors should be used for each pin.



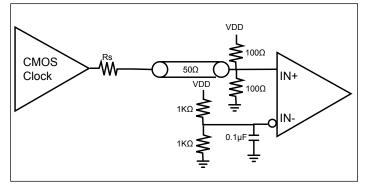




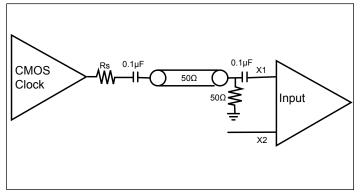
Single-Ended Input, AC Couple



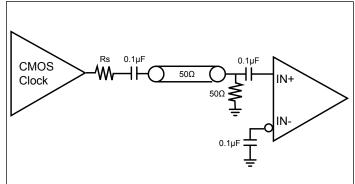
Single-Ended Input, DC Couple



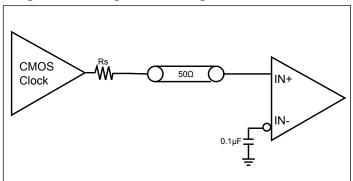
Driving X1 with a Single-Ended Input



Single-Ended Input, AC Couple



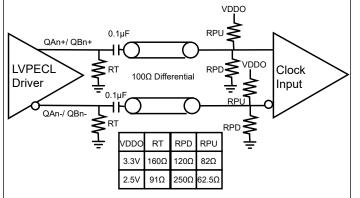
Single-Ended Input, DC Couple



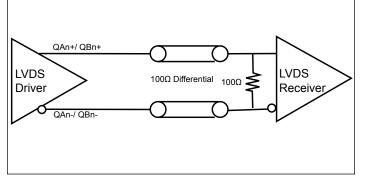




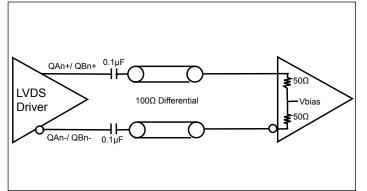
LVPECL, AC Couple, Thevenin Equivalent



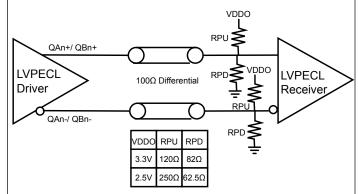
LVDS DC Couple



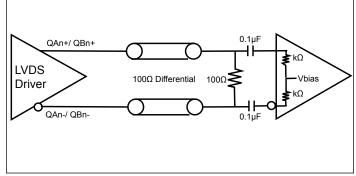
LVDS AC Couple with Internal Termination



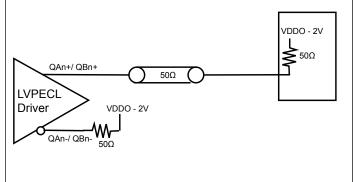
LVPECL, DC Couple, Thevenin Equivalent



LVDS AC Couple at Load



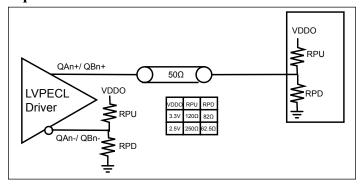
Single-Ended LVPECL, DC Couple



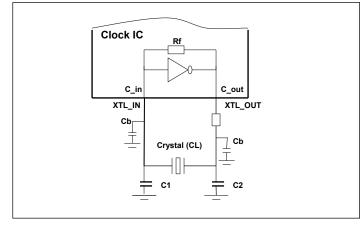




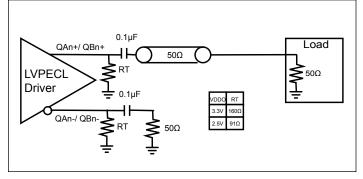
Single-Ended LVPECL, DC Couple, Thevenin Equivalent



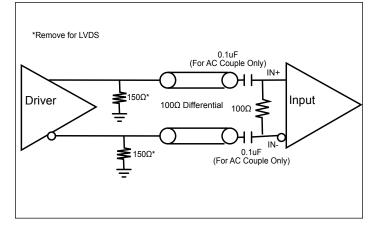
Clock IC Crystal Input Guide



Single-Ended LVPECL, AC Couple, Thevenin Equivalent



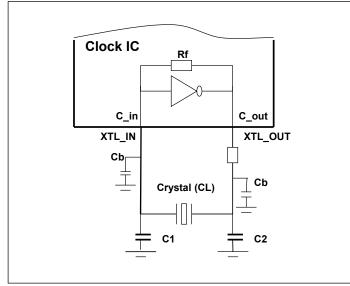
LVPECL/LVDS AC and DC Input







Clock IC Crystal Loading Cap. Design Guide



CL = crystal spec. loading cap. $C_in/out = (3pF \sim 5pF)$ of IC pin cap. $Cb = PCB \text{ trace } (2pF \sim 4pF)$ C1,C2 = load cap. of design $Rd = 50\Omega$ to 100Ω drive level limit

Design guide: $C1 = C2 = 2 \times CL - (Cb + C_in/out)$ to meet target $\pm ppm < 20ppm$

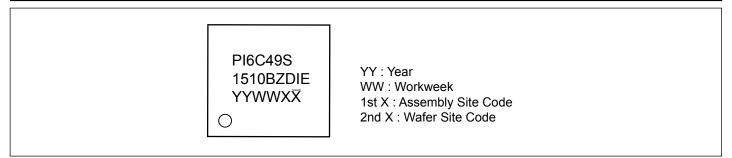
Example 1: Select CL = 18pF crystal, $C1 = C2 = 2 \times (18pF) - (4pF + 5pF) = 27pF$. Check datasheet.

Example 2: For higher frequency crystal (= >20MHz), the following formula can be used: $C1 = C2 = 2 \times (CL - 6)$. A fine tune of C1, C2 can be used for more accurate ppm if necessary.

Thermal Information

Symbol	Description	Condition	_
Θ_{JA}	Junction-to-Ambient Thermal Resistance	Still air	23.65°C/W
$\Theta_{\rm JC}$	Junction-to-Case Thermal Resistance		9.1°C/W

Part Marking

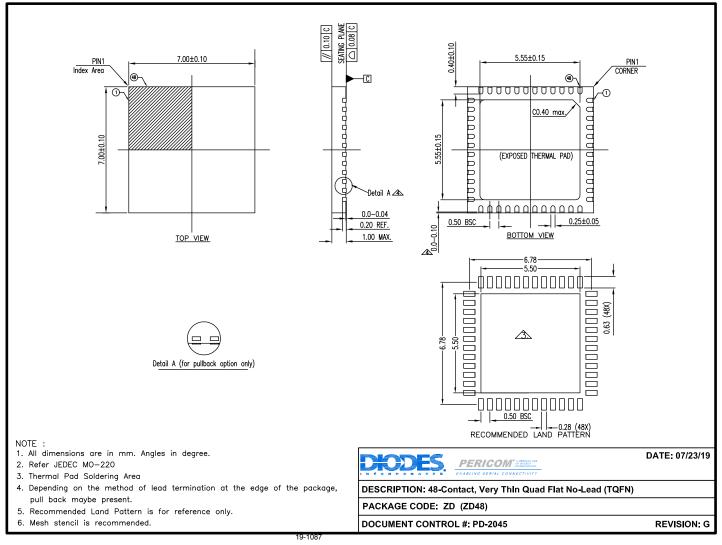






Packaging Mechanical

48-TQFN (ZD)



For latest package information:

 $See \ http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/.$

Ordering Information

Ordering Code	Package Code	Package Type	Operating Temperature
PI6C49S1510BZDIEX	ZD	48-Contact, Very Thin Quad Flat No-Lead (TQFN)	-40°C to 85°C

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

- 4. I = Industrial
- 5. E = Pb-free and Green
- 6. X suffix = Tape/Reel





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